

Product Summary

Device	BV _{DSS}	R _{DS(ON)} MAX	I _D T _A = +25°C
Q2	40V	24mΩ @ V _{GS} = 10V	9.0A
		32mΩ @ V _{GS} = 4.5V	7.8A
Q1	-40V	45mΩ @ V _{GS} = -10V	-6.5A
		55mΩ @ V _{GS} = -4.5V	-5.9A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

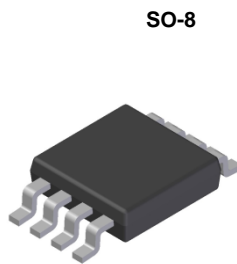
- DC-DC converters
- Power-management functions
- Backlighting

Features and Benefits

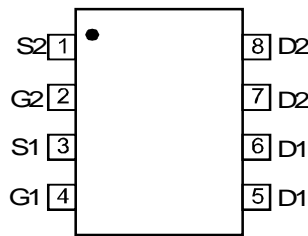
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.** <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

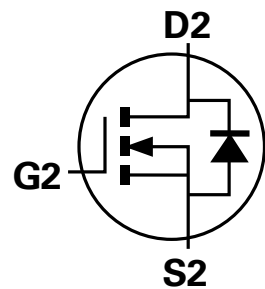
- Package: SO-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.074 grams (Approximate)



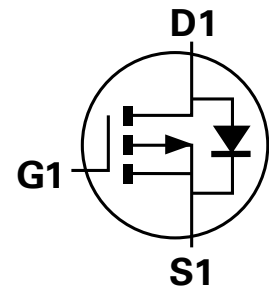
Top View



Top View
Internal Schematic



N-Channel MOSFET



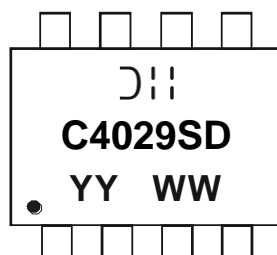
P-Channel MOSFET

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMC4029SSD-13	SO-8	2500	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DII = Manufacturer's Marking
 C4029SD = Product Type Marking Code
 YYWW or YYWW = Date Code Marking
 YY or YY = Year (ex: 24 = 2024)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value_Q2	Value_Q1	Unit
Drain-Source Voltage			V _{DSS}	40	-40	V
Gate-Source Voltage			V _{GSS}	±20	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	7.0 5.6	-5.1 -4.1	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	9.0 7.2	-6.5 -5.2	A
Maximum Body Diode Forward Current (Note 6)			I _S	2.5	-2.5	A
Pulsed Drain Current (10μs pulse, Duty Cycle = 1%)			I _{DM}	70	-40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.3	W
	T _A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	98	°C/W
	t < 10s		59	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.8	W
	T _A = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	71	°C/W
	t < 10s		43	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	11.8	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics N-Channel Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	15	24	mΩ	V _{GS} = 10V, I _D = 6A
		—	20	32		V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1060	—	pF	V _{DS} = 20V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	84	—		
Reverse Transfer Capacitance	C _{RSS}	—	58	—		
Gate Resistance	R _G	—	1.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	8.8	—	nC	V _{DS} = 20V, I _D = 8A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	19.1	—		
Gate-Source Charge	Q _{GS}	—	3.0	—		
Gate-Drain Charge	Q _{GD}	—	2.5	—		
Turn-On Delay Time	t _{D(ON)}	—	5.3	—	ns	V _{DD} = 25V, R _L = 2.5Ω V _{GS} = 10V, R _G = 3Ω
Turn-On Rise Time	t _R	—	7.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	15.1	—		
Turn-Off Fall Time	t _F	—	4.8	—		
Body Diode Reverse Recovery Time	t _{RR}	—	10.5	—	ns	I _F = 8A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	4.15	—	nC	I _F = 8A, di/dt = 100A/μs

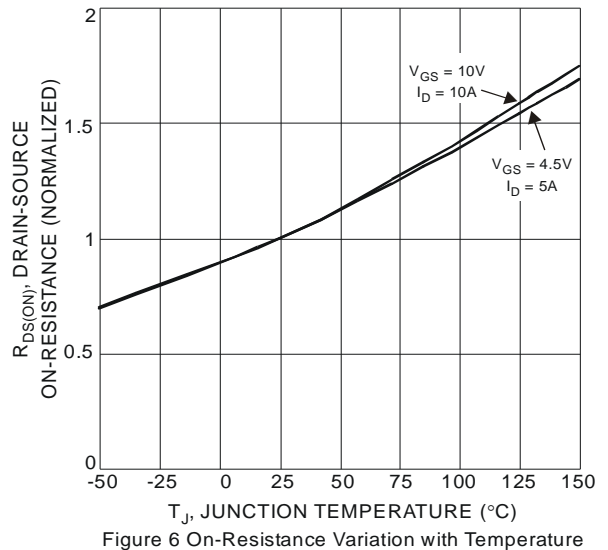
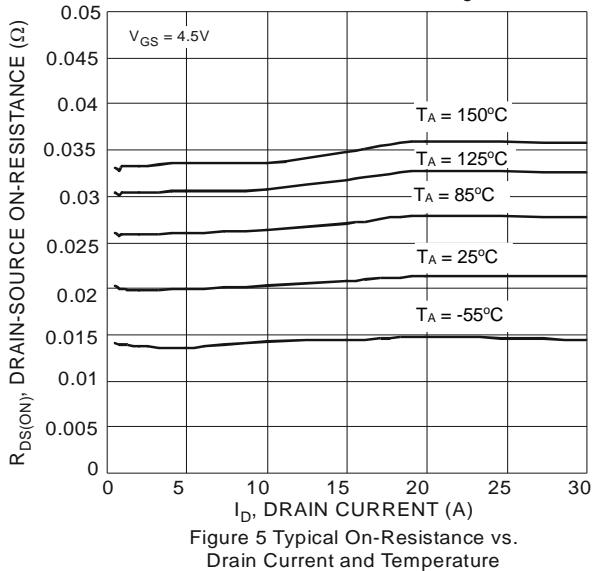
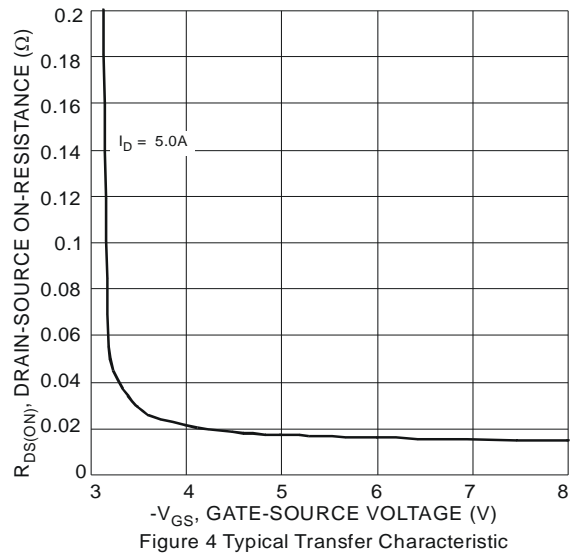
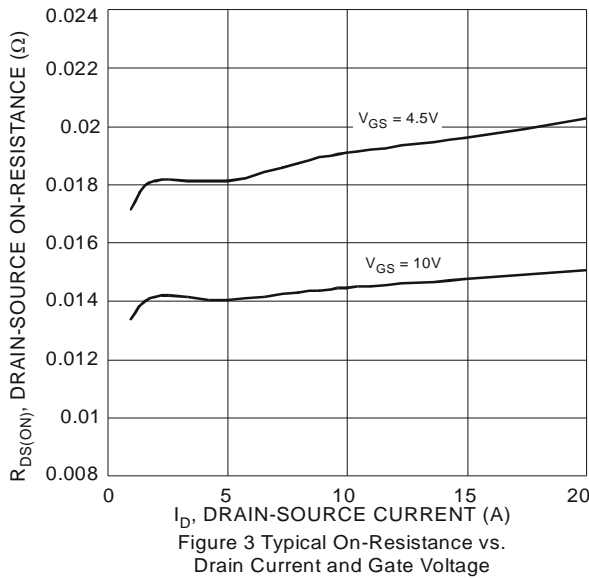
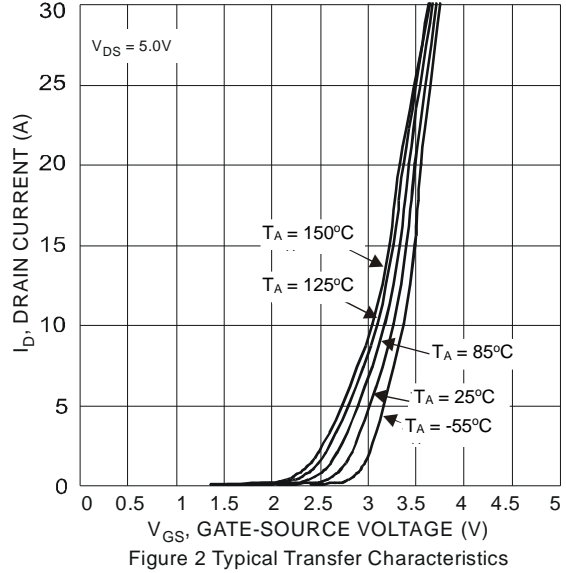
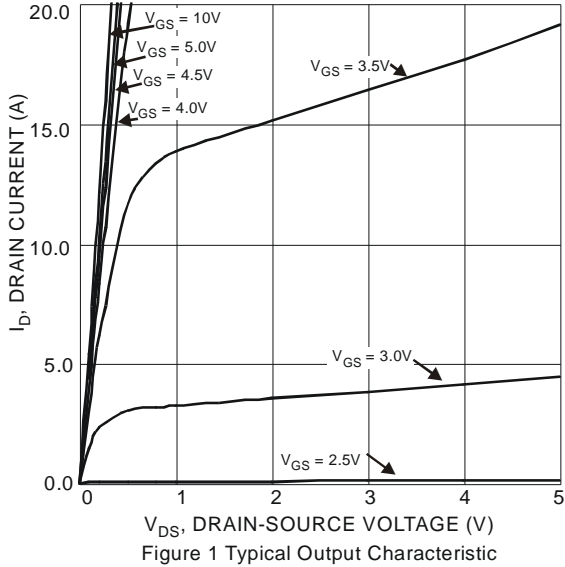
- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

Electrical Characteristics P-Channel Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-40	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -40V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	33	45	mΩ	V _{GS} = -10V, I _D = -5A
		—	40	55		V _{GS} = -4.5V, I _D = -4A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1154	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	84	—		
Reverse Transfer Capacitance	C _{rss}	—	66	—		
Gate Resistance	R _g	—	12.6	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	10.6	—	nC	V _{DS} = -20V, I _D = -4.9A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	21.5	—		
Gate-Source Charge	Q _{gs}	—	2.2	—		
Gate-Drain Charge	Q _{gd}	—	3.3	—		
Turn-On Delay Time	t _{D(ON)}	—	8.7	—	ns	V _{DS} = -20V, I _D = -3.9A V _{GS} = -4.5V, R _G = 1Ω
Turn-On Rise Time	t _R	—	19.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	34.9	—		
Turn-Off Fall Time	t _F	—	25.5	—		
Body Diode Reverse Recovery Time	t _{RR}	—	9.61	—	ns	I _S = -3.9A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	3.3	—	nC	I _S = -3.9A, di/dt = 100A/μs

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

N-Channel Q2



N-Channel Q2 (continued)

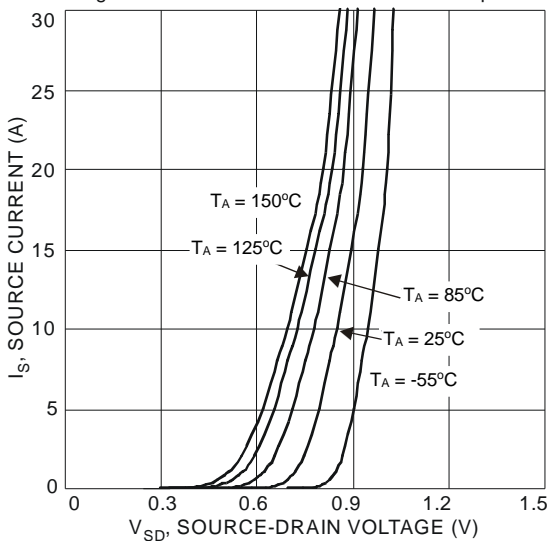
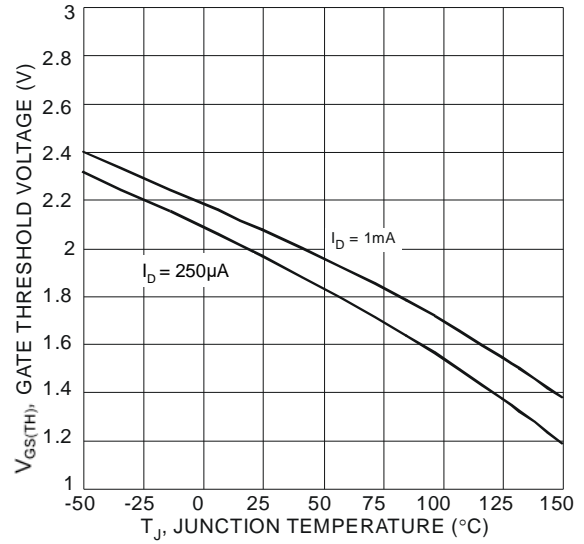
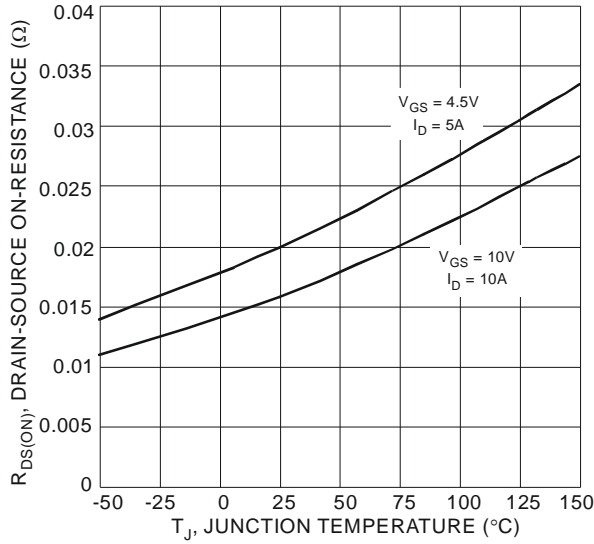
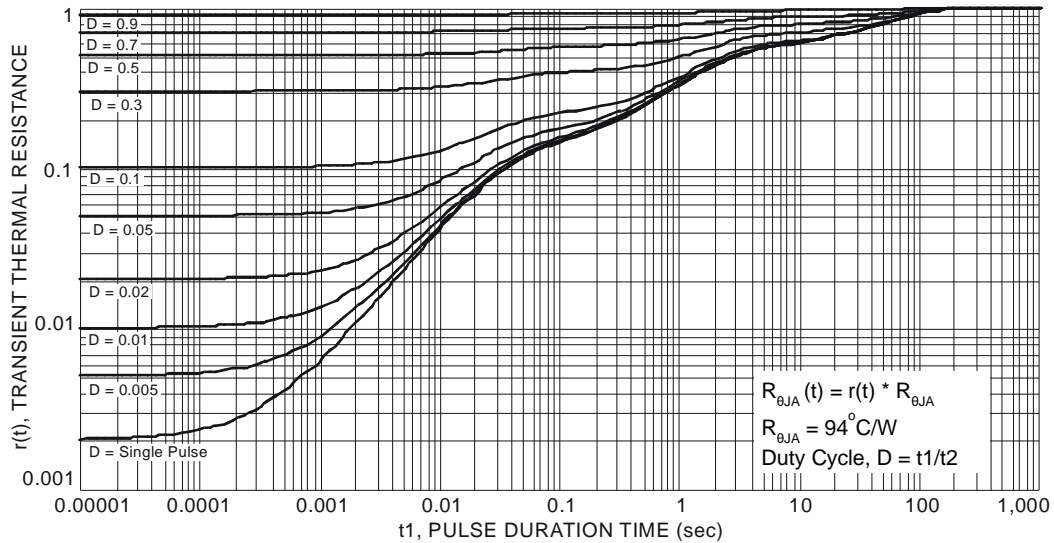


Figure 9 Diode Forward Voltage vs. Current



P-Channel Q1

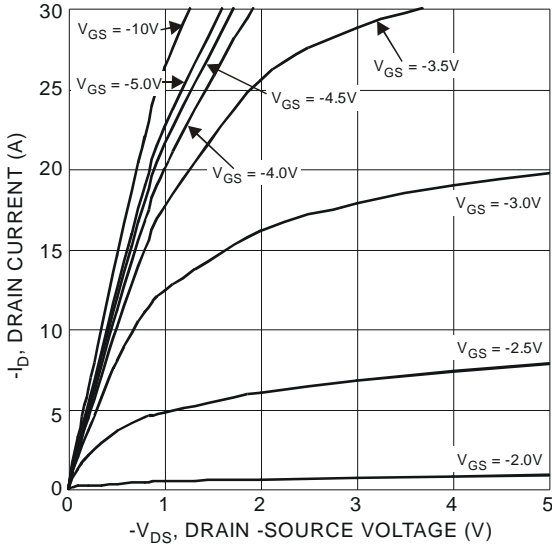


Figure 11 Typical Output Characteristics

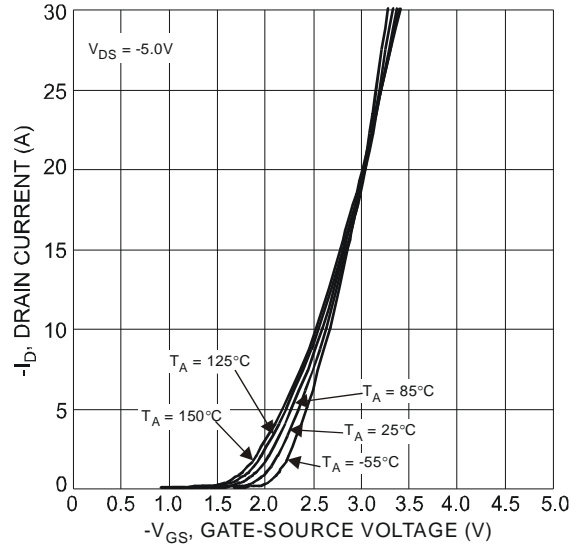


Figure 12 Typical Transfer Characteristics

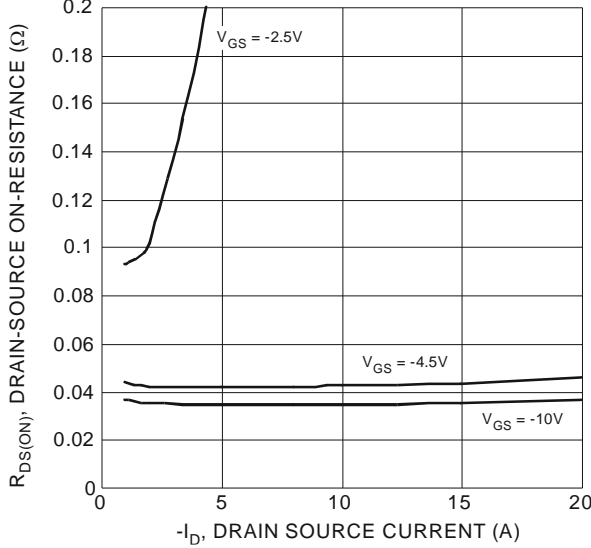


Figure 13 Typical On-Resistance vs. Drain Current and Gate Voltage

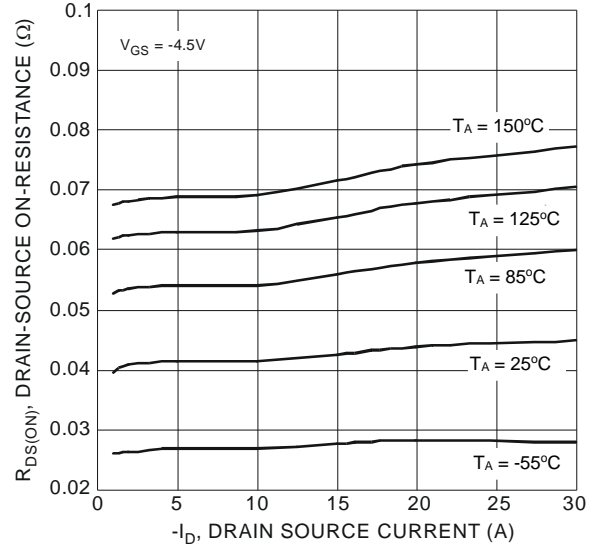


Figure 14 Typical On-Resistance vs. Drain Current and Temperature

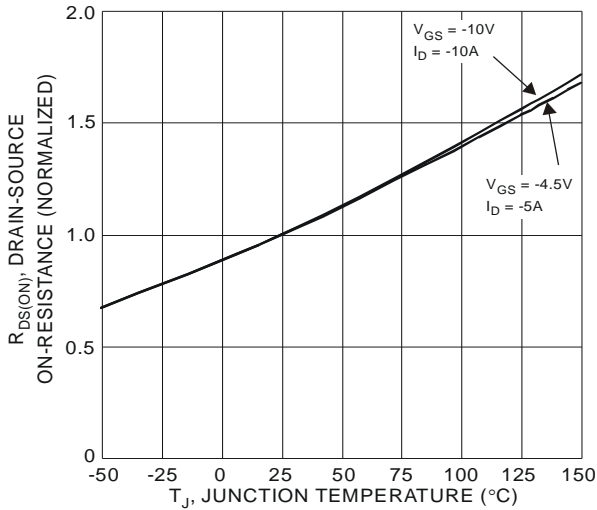


Figure 15 On-Resistance Variation with Temperature

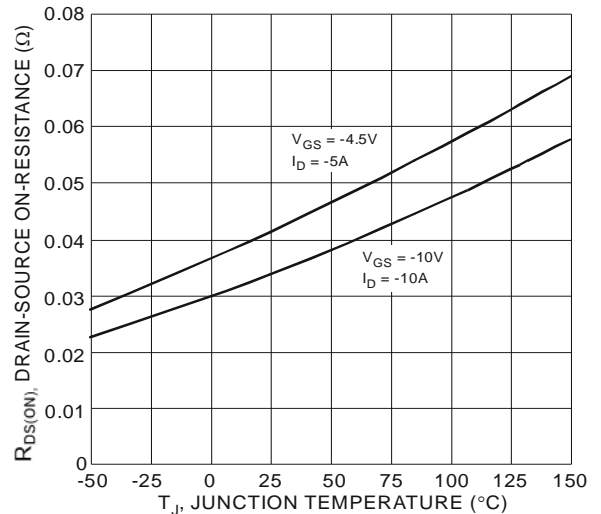


Figure 16 On-Resistance Variation with Temperature

P-Channel Q1 (continued)

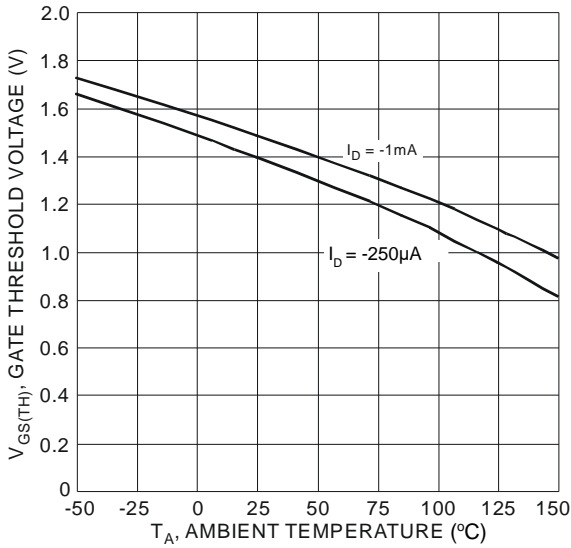


Figure 17 Gate Threshold Variation vs. Ambient Temperature

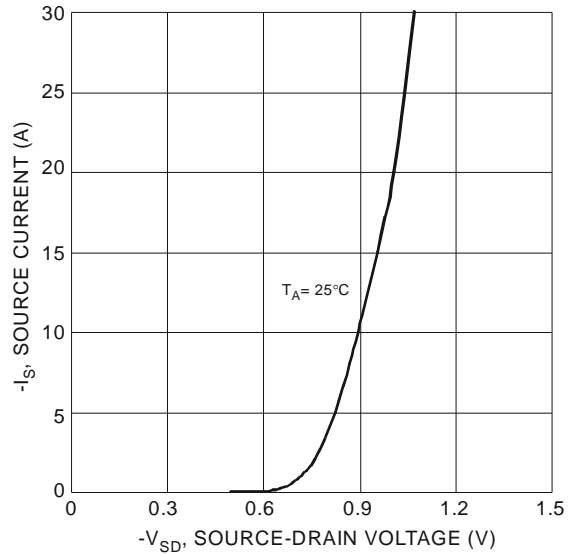


Figure 18 Diode Forward Voltage vs. Current

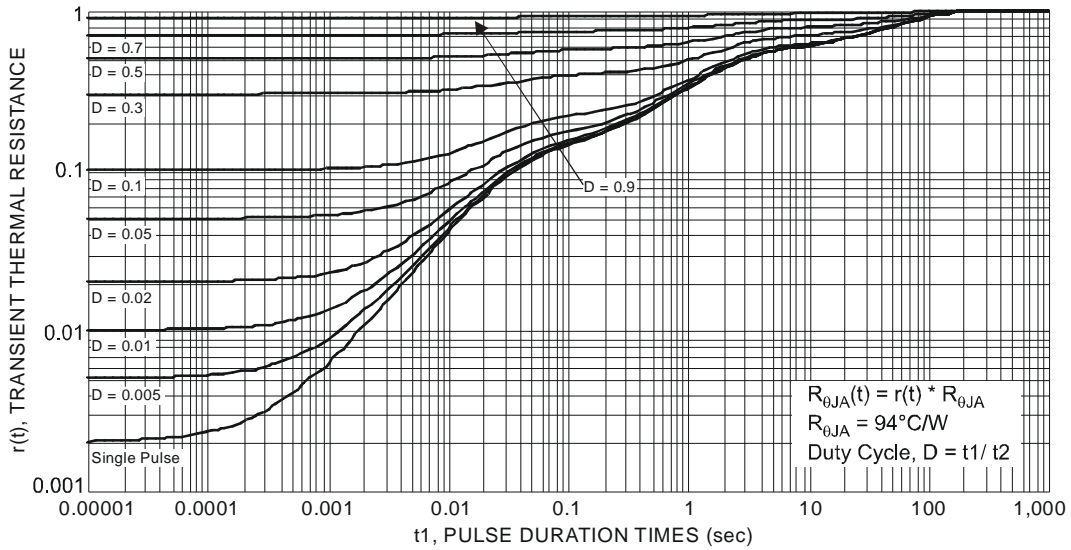
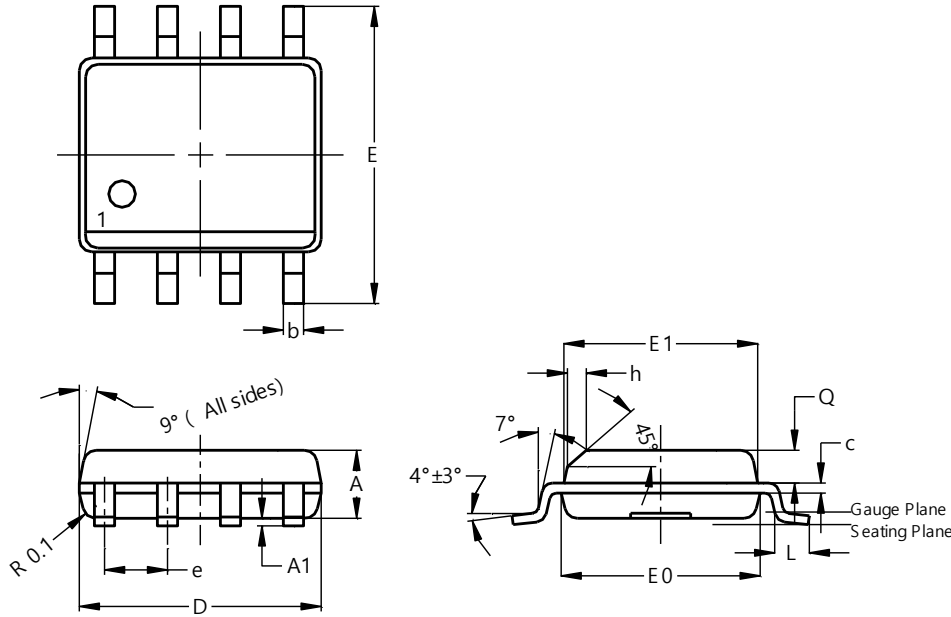


Figure 19 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

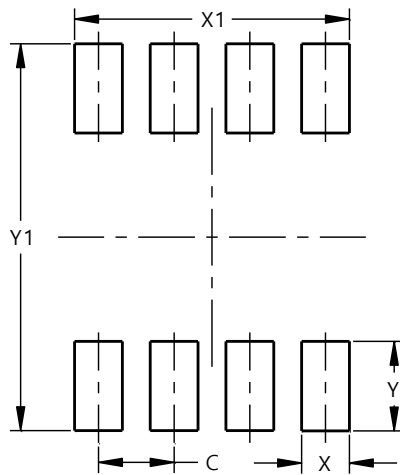


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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